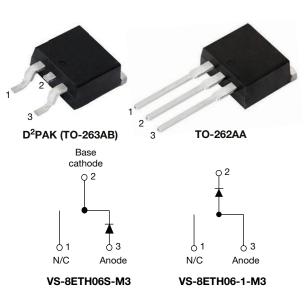
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## **Vishay Semiconductors**

Hyperfast Rectifier, 8 A FRED Pt<sup>®</sup>



## LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	8 A				
V <sub>R</sub>	600 V				
V <sub>F</sub> at I <sub>F</sub>	1.3 V				
t <sub>rr</sub> typ.	18 ns				
T <sub>J</sub> max.	175 °C				
Package	D <sup>2</sup> PAK (TO-263AB), TO-262AA				
Circuit configuration	Common cathode				

#### FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

## **MECHANICAL DATA**

Case: D<sup>2</sup>PAK (TO-263AB), TO-262AA

Molding compound meets UL 94 V-0 flammability rating

**Terminals:** matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage	V <sub>RRM</sub>		600	V
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 144 °C	8	
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	90	А
Peak repetitive forward current	I <sub>FM</sub>		16	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C

ELECTRICAL SPEC	IFICATIO	<b>NS</b> ( $T_J = 25 \ ^{\circ}C$ unless otherwise specified	d)			
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	600	-	-	
Forward voltage	VF	I <sub>F</sub> = 8 A	-	2.0	2.4	V
Forward voltage	۷F	I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	1.3	1.8	
Roverse leakage ourrest	1-	$V_{R} = V_{R}$ rated	-	0.03	50	
Reverse leakage current	I <sub>R</sub>	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	55	500	μA
Junction capacitance	CT	V <sub>R</sub> = 600 V	-	17	-	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH

Revision: 08-Apr-2024

Document Number: 96387

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COMPLIANT

HALOGEN

FREE



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DYNAMIC RECOVERY CHARACTERISTICS (T <sub>C</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 1$	00 A/µs, V <sub>R</sub> = 30 V	-	18	22	
Reverse recovery time	+	$I_F = 8 A$ , $dI_F/dt = 1$	00 A/µs, V <sub>R</sub> = 30 V	-	20	25	ns
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	-	115
		T <sub>J</sub> = 125 °C		-	40	-	
Peak recovery current	1	T <sub>J</sub> = 25 °C	l <sub>F</sub> = 8 A dl <sub>F</sub> /dt = 200 A/μs	-	2.4	-	А
Feak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$V_{\rm R} = 390 \text{ V}$	-	4.8	-	~
	0	T <sub>J</sub> = 25 °C		-	25	-	nC
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	120	-	nc
Reverse recovery time	t <sub>rr</sub>		I <sub>F</sub> = 8 A	-	33	-	ns
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 600 A/µs	-	12	-	А
Reverse recovery charge	Q <sub>rr</sub>		V <sub>R</sub> = 390 V	-	220	-	nC

THERMAL - MECHANICAL SPE	CIFICATIO	DNS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	1.4	2	
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.5	-	
Weight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking davias		Case style D <sup>2</sup> PAK (TO-263AB)		8ETH	106S	°C/W g oz. kgf · cm
Marking device		Case style TO-262AA	8ETH06-1			

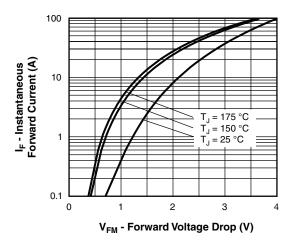
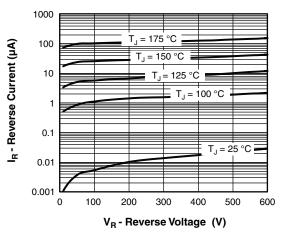
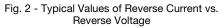


Fig. 1 - Maximum Forward Voltage Drop Characteristics







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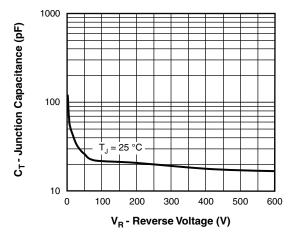


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

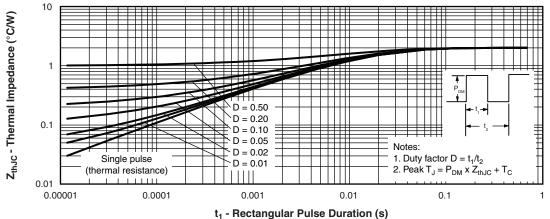
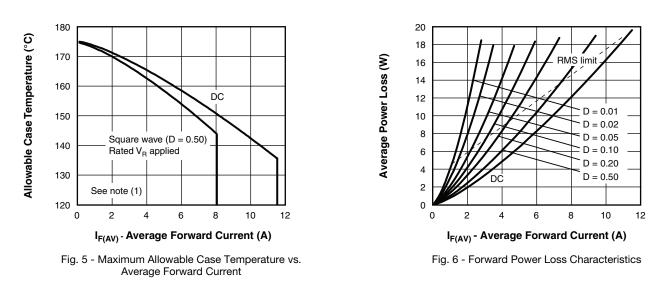


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



Revision: 08-Apr-2024

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## VS-8ETH06S-M3, VS-8ETH06-1-M3

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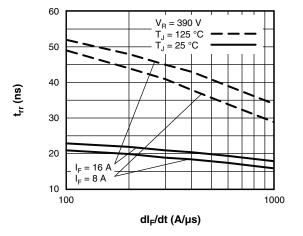


Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

#### Note

- <sup>(1)</sup> Formula used:  $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$ ;
- Pd = forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 6); Pd<sub>REV</sub> = inverse power loss =  $V_{R1} \times I_R$  (1 - D);  $I_R$  at  $V_{R1}$  = rated  $V_R$

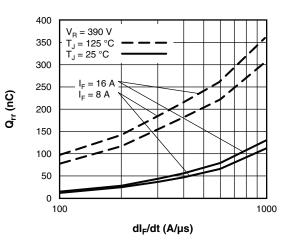


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

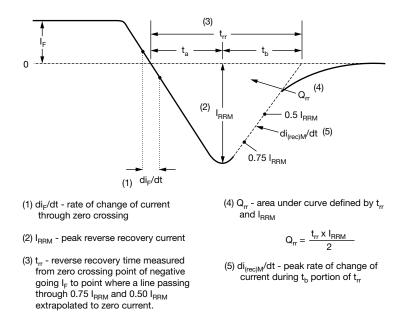


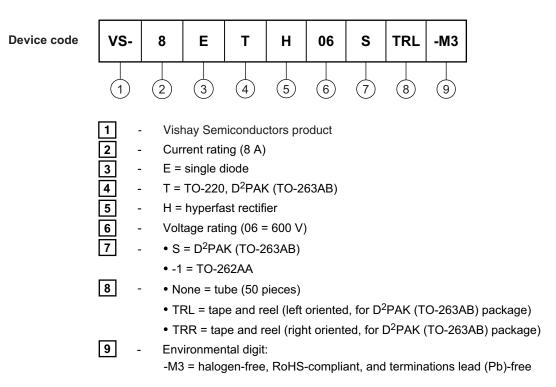
Fig. 9 - Reverse Recovery Waveform and Definitions

# VS-8ETH06S-M3, VS-8ETH06-1-M3

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#### **ORDERING INFORMATION TABLE**

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<b>ORDERING INFORMATION</b> (Exan	nple)	
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION
VS-8ETH06S-M3	50	Antistatic plastic tubes
VS-8ETH06STRL-M3	800	13" diameter plastic tape and reel
VS-8ETH06STRR-M3	800	13" diameter plastic tape and reel
VS-8ETH06-1-M3	50	Antistatic plastic tubes

	LINKS TO RELATE	D DOCUMENTS
Dimensions —	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96164
	TO-262AA	www.vishay.com/doc?96165
Port marking information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?95444
Part marking information —	TO-262AA	www.vishay.com/doc?95443
Packaging information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96424

**Vishay Semiconductors** 

D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625		
L	1.78	2.79	0.070	0.110		
L1	-	1.65	-	0.066	3	
L2	1.27	1.78	0.050	0.070		
L3	0.25	BSC	0.010	BSC		
L4	4.78	5.28	0.188	0.208		

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

Revision: 13-Jul-17

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Document Number: 96164

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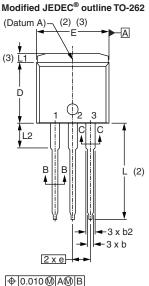
## **Outline Dimensions**

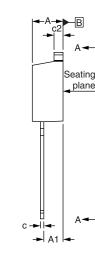


**Vishay Semiconductors** 

**TO-262AA** 

#### **DIMENSIONS** in millimeters and inches





F D1 (3) (3) Section A - A Base (4) Plating b1. b3 metal ≰ c1 (4) -(b, b2)-Section B - B and C - C Scale: None





Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode

Lead assignments

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100	) BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

 <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the second dimensioner of the second dimensis of the second dimensioner of the second dimensioner of the the outmost extremes of the plastic body (3)

Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only (5)

Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17

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Revision: 01-Jul-2024